Electron Spin Dynamics in Impure Quantum Wells for Arbitrary Spin-Orbit Coupling

## C.Grim aldi

Ecole Polytechnique Federale de Lausanne, LPM, Station 17, CH-1015 Lausanne, Switzerland

Strong interest has arisen recently on low-dimensional systems with strong spin-orbit interaction due to their enhanced eciency in some spintronic applications. Here, the time evolution of the electron spin polarization of a disordered two-dimensional electron gas is calculated exactly within the Boltzmann formalism for arbitrary couplings to a Rashba spin-orbit eld. It is shown that the classical Dyakonov-Perelmechanism of spin relaxation gets deeply modied for su ciently strong Rashba elds, in which case new regimes of spin decay are identied. These results suggest that spin manipulation can be greatly in proved in strong spin-orbit interaction materials.

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The physics of transport of electron spins in lowdim ensional systems has become a popular theme of research due to the possible impact in future electronic applications[1, 2]. Key subjects of studies concern the problem of controlling the electron spin polarization through the tailoring of the spin-orbit (SO) interaction [3, 4], and the know ledge of the physical param eters goveming the spin relaxation time s. Main sources of SO coupling are the Rashba interaction arising from structural inversion asymmetries of low-dimensional structures such as quantum wells or wires[5], and the D resselhaus interaction present in bulk crystals lacking symm etry of inversion [6]. In the presence of Rashba and/or D resselhaus interactions,  $_{\rm s}$  basically arises from the random ization of the SO (pseudo)m agnetic eld induced by m om entum scattering with impurities or other interactions (Dyakonov-Perelmechanism [7]).

Of great interest for spintronic applications are materials with strong SO interaction since they are more effective spin-m anipulators [2] and spin-current generators through the spin-Halle ect [8]. In this respect, systems of interest may be, for example, HgTe quantum wells whose Rashba interaction leads to SO band splitting so 30 m eV [9], or surface states of m etals and as large as sem im etals which display giant SO band splittings of the order of 0.2 eV or surface states of m etals and sem im etals which display giant SO band splittings of the order of 0.2 eV or larger [10, 11], or even the heavy Ferm ion superconductor CePt3Si [12] whose lack of bulk inversion sym m etry leads to so ' 50 200 m eV [13]. For all these systems, the SO splitting  $_{\rm so}$  is no longer the sm allest energy scale, as in most sem iconductors, and can be comparable to the Fermi energy F or even larger.

D espite that the time evolution of the spin polarization S has been thoroughly studied in the weak SO limit  $_{so}=_F=0$  [7, 14, 15, 16], only few partial studies have been devoted to the strong SO case  $_{so}=_F$  6 0 [17, 18, 19]. Of particular interest is the problem of assessing the role of  $_{so}=_F$  on the spin relaxation mechanism and of clarifying to which extent the classical D yakonov-Perel (DP) description [7] gets modiled by nite values of  $_{so}=_F$ .

In this letter, a generalized kinetic equation for S is formulated for arbitrary strengths of the SO interaction and in the presence of spin-conserving coupling with impurities. For the case of a two-dim ensional electron gas con ned in the x y plane subjected to the Rashba interaction, the kinetic equation for the z-com ponent of S is solved explicitly for any value of  $_{so} = _{F}$ . It is found that for a su ciently strong Rashba interaction the DP relaxation mechanism gets modi ed, with the spin polarization displaying a slow (power law) decay with time. Furtherm ore, in the extrem  $e_{so} = F$ 1 lim it, a fast exponential decay is obtained with s proportional to the m om entum scattering time p, i.e., spin relaxation is enhanced by disorder. These ndings suggest that tailoring of spin m em ory through  $_{\infty}$  =  $_{\rm F}$  can be much more e ective than previously thought.

Let us consider an electron gas whose non-interacting ham iltonian H  $_{\rm 0}$  is:

$$H_{0} = X_{k,s} c_{k,s}^{y} c_{k,s} + \frac{\sim}{2} X_{k,ss^{0}} k b_{ss^{0}} c_{k,s}^{y} c_{k,s^{0}}; \qquad (1)$$

where  $c_{k\,s}^y$  ( $c_{k\,s}$ ) is the creation (annihilation) operator for an electron with momentum k and spin index s=";#,b is the spin-vector operator with components ( $b^x;b^y;b^z$ ) given by the Paulim atrices, and  $_k$  is a k dependent SO pseudopotential vector whose explicit form is not essential for the moment. In the above expression,  $_k$  is the electron dispersion in the absence of SO coupling. Let us consider as momentum -relaxation mechanism a coupling  $V_{k\,k^0}$  to spin-conserving in purities located at random positions R  $_i$ . A dditional interaction channels as those provided by phonons or electron-electron couplings can be treated as well by following the same steps described below. A ssuming that  $V_{k\,k^0}$  is switched on at time  $t=t_0$ , the time evolution of S (t) for  $t>t_0$  can be obtained from the equation of motion of the density matrix (t) [20]:

$$\frac{\mathrm{d}b_{kk^{\circ}}(t)}{\mathrm{d}t} = -\frac{\mathrm{i}}{\sim} \mathbb{E}_{k} b_{kk^{\circ}}(t) - b_{kk^{\circ}}(t) \mathbb{E}_{k^{\circ}} - \frac{\mathrm{i}}{\sim} b_{kk^{\circ}}(t);$$
(2)

where  $b_{kk^0}$  (t) is a 2 2 m atrix with elements  $k_{s;k^0s^0}$  (t) =

hksj (t) 
$$k^0 s^0 i$$
,  $k^0 k^0 k$  =  $k$  +  $\frac{2}{2} k$  b, and 
$$b_{kk^0}(t) = V_{kp} e^{iR_i (k p)} b_{pk^0}(t)$$

$$V_{kp} e^{iR_i (p k)} b_{kp}(t)$$

$$V_{kp} e^{iR_i (p k)} b_{kp}(t)$$

$$(3)$$

Equation (2) can be formally integrated and, after the usual adiabatic (t<sub>0</sub> ! 1 ) and M arkov approximations [20, 21],  $b_{k\,k^0}$  (t) can be expressed as:

$$b_{kk^{0}}(t)$$
,  $\frac{1}{2} \sum_{k=0}^{Z-1} dt^{0} e^{-t^{0}} e^{-it^{0}_{kk}t^{0} = -k} b_{kk^{0}}(t) e^{-it^{0}_{k^{0}}t^{0} = -k}$  (4)

where the  $\lim$  it! O' must be taken after the integration. By using the anticom mutation property of the

Pauli matrices,  $b_ib_j + b_jb_i = \mathcal{P}_{ij}$ , the exponential operators in Eq.(4) can be put in a form more suitable for integration over  $t^0$ :

$$e^{i b_k t^0 = \infty} = \frac{1}{2}^X$$
  $e^{i E_k t^0 = \infty} (1 + {^{\hat{k}}} b);$  (5)

where = 1,  $\hat{k} = \hat{k} = \hat{j}_k \hat{j}$  and  $\hat{E}_k = \hat{k} = \hat{k} = \hat{j}_k \hat{j}$  are the eigenvalues of  $\hat{H}_0$  [Eq.(1)]. At this point, averaging over the impurity positions  $\hat{R}_i$  restores the translational invariance:  $\hat{h}_{kk^0}$  (t)  $\hat{i}_{imp} = \hat{k}_{ijk^0}\hat{b}_k$  (t), and, nally, the equation of motion of electron spins for a given wave vector  $\hat{k}$ ,  $\hat{S}_k = \hat{j}_2 Tr(\hat{b}_k)$ , is obtained by integrating over  $\hat{t}_0$ . By retaining only the scattering contributions (Boltzmann approximation) [19], the nal result is therefore:

$$\frac{dS_{k}}{dt} = {}_{k} S_{k} \frac{2 n}{2} \sum_{p}^{X} V_{pk}^{2} \frac{1}{4} \sum_{p}^{X} \left[ L \left( \hat{k} \hat{p} \right) \right] (S_{k} S_{p}) + \hat{k} \left[ \hat{p} (S_{p} S_{p}) \right] + \hat{p} \left[ \hat{k} (S_{p} S_{p}) \right] + \hat{k} \left[ \hat{p} (S_{p} S_{p}) \right] + \hat{k} \left[ \hat{p} (S_{p} S_{p}) \right] + \hat{k} \left[ \hat{k} (S_{p} S_{p}) \right] + \hat{k} \left$$

where n is the impurity concentration and  $f_k = \frac{1}{2} Tr \langle P_k \rangle$ is the electron occupation distribution function. Equation (6) is very general, and holds true for both bulk and low-dim ensional systems with no restrictions on the particular form of k. In this letter, Eq.(6) is used to nd the time evolution of the electron spin polarization  $S = \bigcup_{k} S_k$  for a two-dim ensional electron gas con ned in the x y plane and subjected to a Rashba SO interaction. In such a case, the e ective SO  $k = (R k_y; R k_x; 0)$  and the corresponding SO split bands depend solely on the magnitude k of the wave vector and can be written as E  $_k$  = E  $_k$  =  $\frac{^2}{2m}$  (k +  $k_R$ ) $^2$ , where m is the electron mass and  $k_R \ \stackrel{\text{....}}{=} \ \frac{m}{2^{\sim}} \ _R$  [22]. In the following, instead of using  $_{so}$  =  $_{R}$   $k_{F}$ , the SO splitting will be param etrized by the Rashba energy  $_R=\frac{\sim^2k_R^2}{2m}=\frac{m}{8}$  , that is the m in in um inter-band excitation energy for an electron sitting at the bottom of the lower band [see Fig.1(a)].

By assuming that the momentum dependence of the impurity potential can be neglected,  $V_{kp}=V$ ,  $S_k$  is conveniently decomposed in its even,  $S_k^{\rm e}$ , and odd,  $S_k^{\rm o}$ , parts with respect to k. It is then clear that  $S={}_kS_k^{\rm e}$  and, from Eq.(6), dS=dt= ${}_kS_k={}_kS_k={}_kS_k^{\rm o}$ , where  ${}_p={}_k$  has been used. O fcourse, dS=dt is also equal to  ${}_kdS_k^{\rm e}$ =dt, so that, after a further derivative with respect to time, the equation of motion can be recast in the following form:

$$\frac{X}{dt^2} = \frac{d^2 S_k^e}{dt^2} \qquad k \quad \frac{dS_k^o}{dt} = 0:$$
 (7)

By taking the vector product with  $_k$ , the odd part of Eq.(6) can be rewritten as:

$$\frac{dS_{k}^{\circ}}{dt} = k \left( k S_{k}^{e} \right) \frac{2 \text{ nV}^{2} X}{4^{\circ}} X \left[ k S_{k}^{\circ} \right] + \frac{k}{p} S_{p}^{\circ} \frac{k}{p} k \left( S_{p}^{\circ} \right)^{\circ} k \right]$$

$$(E_{k} E_{p}); \qquad (8)$$

where the summation over momenta has cancelled all terms odd in p and the identity  $(^{\circ}_{k} \quad ^{\circ}_{p})(_{k} \quad S_{p}^{\circ})(_{k} \quad S_{p}^$ 

$$\frac{dS_{k}^{e}}{dt} = k S_{k}^{o} \frac{2 nV^{2} X X}{4^{-}} (S_{k}^{e} S_{p}^{e} + \hat{S}_{p}^{e}) (E_{k} E_{p}); (9)$$

where  $f_k^{\circ} = \frac{1}{2} (f_k + f_k)$  is the odd part of  $f_k$ .

By using Eqs.(8) the term  $_k$   $dS_k^\circ=dt$  in Eq.(7) can be elim inated in favor of  $S_k^\circ$  and  $S_k^\circ$ . Next, by using Eq.(9), also the terms containing  $S_k^\circ$  can be elim inated and Eq.(7) reduces to an equation of motion of the component  $S_k^\circ$  only, that is sudient to indicate the time evolution of  $S=\frac{1}{k}S_k^\circ$ . Let us consider the z-component of  $S,S_z$ , for which the presence of  $S_k^\circ$  in Eq.(9) has not expected by each of these terms have zero component in the z-direction.

In this way, Eq.(7) reduces to:

$$\frac{Z}{0} \frac{1}{2} \frac{dkk}{2} \frac{d^2S_{zk}^e}{dt^2} + \frac{2}{R}k^2 + \frac{k}{4\frac{2}{p}} S_{zk}^e + \frac{k}{p} \frac{dS_{zk}^e}{dt} = 0;$$
(10)

where  $S_{zk}^e = \frac{R_2}{_0}$  d  $S_{zk}^e = 2$ , with being the angle between the directions of k and the x-axis,  $_p^{-1} = \frac{2}{_{\sim}} nV^2 N_0$  is the momentum relaxation rate for a two-dimensional electron gas with zero SO splitting and density of states (DOS)  $N_0 = m = 2$   $\sim^2$ , and:

$$k = \frac{1}{4N_0} X^{\frac{Z}{1}} \frac{1}{2} \frac{dpp}{2} 1 + \frac{p}{k} (E_k E_p); (11)$$

$$k = \frac{1}{N_0} X^{\frac{Z}{1}} \frac{dpp}{2} (k_p) (E_k E_p); (12)$$

A solution to Eq.(10) is obtained by equating to zero the expression within square brackets, which leads to a homogeneous differential equation of the second order for  $S_{zk}^e$  (t). In this way the functions  $_k$  and  $_k$  assume respectively the meaning of renormalization of the damping term and of shift of the (bare) precessional frequency  $_R$  k. It can be easily realized from Eqs.(11,12) that in the weak SO  $\lim_{k \to \infty} f_k = 1$ , for which  $E_k = \frac{2^k k^2}{2m}$ , both the damping renormalization and the frequency shift are absent ( $_k = 1$  and  $_k = 0$ ), indicating that these quantities stem from additional intra-and inter-band scattering channels opened when  $_F = _R$  is nite. Let us take a closer look at  $_k$  and  $_k$  by performing the integration over p in Eqs.(11,12):

For  $k>4k_R$ ,  $_k$  and  $_k$  are the same as in the zero S0 lim it, while for lower momenta they acquire a strong k dependence (plotted in Fig.1(c)) arising from the combined elect of the reduced dimensionality (D = 2) and the SO interaction. In particular, the divergence of  $_k$  at  $k=k_R$  and those of  $_k$  at  $k=k_R$  and  $k=3k_R$  are due to scattering processes probing the SO induced van H ove singularity of the DOS of the lower sub-band which diverges as N (E)/  $_R$  =E [see Fig.1(b)]. As it is shown below, such strong k dependence has in portant consequences on the spin polarization dynamics.

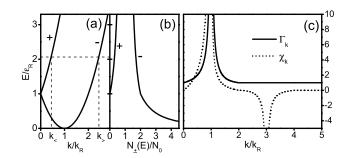


FIG.1: (a): Rashba SO split electron dispersions  $\frac{2}{2m}$  (k  $k_R$ ) in units of  $R = \frac{m}{8}$ . The horizontal dashed line indicates the Fermi level. (b): density of states for the bands. (c): plots of  $R_R$ , Eq.(13), and  $R_R$ , Eq.(14).

Let us now turn to evaluate the explicit time dependence of  $S_z$ . From Eq.(10), a general solution for  $S_{zk}^e$  (t) is given by a linear combination of exp  $\frac{k}{2}\frac{p-k}{k}t$ , where  $k=\frac{2}{k}$  k  $(2_{p-R}k)^2$ , whose coe cients are xed by imposing some initial conditions. If at t=0 electrons have been prepared with a non-equilibrium spinstate occupation but equilibrium distribution for each spin branch then, at the lowest order in the initial weak spin imbalance  $=(-\frac{k}{2})^2$ ,  $S_{zk}^e$  (0) is simply:

$$S_{zk}^{e}(0) = \frac{X}{R^{k}} f_{0}(E_{k});$$
 (15)

where  $f_0(x) = (\exp(x=T) + 1)^{-1}$  is the Ferm i distribution function, T is the temperature and 0 is the chem ical potential. Furthermore, by imposing that  $\lim_{t \ge 1} f_{zk}(t) j < 1$  and by arbitrarily choosing  $dS_z(0) = dt = 0$  for  $p^{-1} = 0$ , at zero temperature ( =  $f_z(0) = 0$ ) is readily found to be:

$$S_{z}(t) = \frac{Z_{k}}{2_{R}} dk \quad (k_{k}) \exp \frac{k_{k} + \frac{p_{k}}{k}}{2_{p}} t + (k_{k}) \exp \frac{k_{k} + \frac{p_{k}}{k}}{2_{p}} t + \cosh \frac{p_{k}}{2_{p}} t; (16)$$

where is the unit step function,  $k_? = k_R$  ( F = R 1) for F = R > 1 and  $k_? = k_R$  (1 F = R) for F = R < 1 [see Fig.1(a)]. For F = R! 1 ,  $k_?$ !  $k_F$  and Eq.(16) reduces to the classical form ula

$$S_z(t) = S_z(0) \exp \frac{t}{2p} \cosh \frac{p}{1 + (2pR)^2}!;$$
(17)

where  $S_z$  (0) =  $\sim$  N<sub>0</sub> and  $_R$  =  $_R$  k $_F$  is the Rashba frequency which characterizes the (damped) spin precession behavior  $S_z$  (t)  $S_z$  (0) exp ( $\frac{t}{2p}$ ) cos( $_R$  t) for 2  $_P$  R 1 and the DP relaxational decay  $S_z$  (t)  $S_z$  (0) exp ( $_P$  R 1  $_R$  t) for 2  $_P$  R 1 [2].

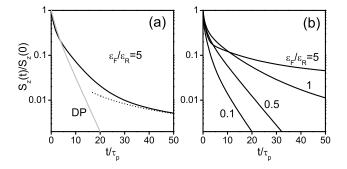


FIG. 2: (a): Spin polarization time evolution from Eq.(16) (solid line) for  $_{\rm P}$  = 3:3 fs,  $_{\rm R}$  = 5 m eV and  $_{\rm F}$  = 25 m eV . The dotted line is the power law decay of Eq.(20) while the grey solid line is Eq.(17). (b): C rossover from the power law decay of (20) and the fast relaxation decay of (21) obtained for  $_{\rm P}$  = 3:3 fs,  $_{\rm F}$  = 5 m eV and several values of  $_{\rm R}$  .

For nite values of  $_F=_R$ , Eq.(16) starts to deviate from the classical regime (17). Let us rst consider  $_F=_R$  25. In this case, the integration over k in Eq.(16) spans values necessarily larger than  $4k_R$ , where, according to Eqs.(13,14),  $_k=1$  and  $_k=0$  [see also Fig.1(c)]. For weak in purity scattering (2  $_P$   $_R$   $k_<$  1)  $_k$  is negative and Eq.(16) reduces to:

$$S_z$$
 (t)  $S_z$  (0) exp  $\frac{t}{2p} = \frac{\sin(s,t) - \sin(s,t)}{(s,s,t)}$ ; (18)

where  $_{?}=_{R}k_{?}$ . The main feature of Eq.(18) is that  $S_{z}$  (t) oscillates with two dierent Rashba frequencies  $_{?}$  associated with the two SO splitted Ferm i surfaces, Fig.1(a). Two distinct Rashba frequencies characterize also the relaxation regime obtained when the scattering with impurities is strong enough that  $2_{R}k_{>}=1$  (and so  $_{R}>0$ ) holds true. Also in this case the integration of Eq.(16) is elementary and

$$S_z(t)$$
  $S_z(0) = \frac{p - erf^{\frac{p}{p}} - erf^{\frac{2}{p}} + erf^{\frac{p}{2}}}{p(s)};$  (19)

where erf is the error function.

The spin precession and relaxation regimes of Eqs.(18,19) are governed solely by the enhanced momentum phase space settled by nite values of F = R. Instead, for  $_{\rm F}$  =  $_{\rm R}$  < 25, also the momentum dependence of  $_{k}$  and  $_{k}$  becomes relevant, leading to important anom alous features of the spin dynamics. One of these is particularly striking and it is found when  $_{\rm F} = _{\rm R}$ 9. In this case, the integration over k in Eq.(16) crosses the point  $k = 2k_R$  where  $p_k$  changes sign [see Fig.1(c)]. Hence, if  $4_p R k_R$ 1, k can be expanded as k ( $2k_R$  k)= $3k_R$  for  $k < 2k_R$ , while when  $k > 2k_R$  k becomes negative leading to exponentially small contributions to  $S_z$  (t) for su ciently long times.

Eq.(16) then can be approximated to:

$$S_z(t)$$
  $\frac{Z_{2k_R}}{2} \frac{dk}{e^{-\frac{(2k_R-k)}{6p^k_R}t}} = \frac{3S_z(0)}{2} \frac{p}{t}$ : (20)

The surprising result of Eq.(20) provides the rather interesting prediction that, for sulciently strong SO interaction and momentum scattering, the spin polarization decays as a power law rather than exponentially. In this case therefore the memory of the initial spin polarization can be much longer lived than in the DP regime, as shown in Fig. 2(a). A nother striking feature is that obtained in the extreme  $_{\rm F}$  =  $_{\rm R}$  1 limit in which the integration of Eq.(16) becomes restricted to a narrow region around  $k = k_{\rm R}$  where both  $_k$  and  $_k$  diverge as  $1 = k_{\rm R}$   $k_{\rm R}$ 

$$S_z(t) / \exp \frac{t}{8_p}$$
; (21)

indicating that for extrem ely strong SO interaction, momentum scattering increases the spin polarization decay. The power decay of (20) and the fast relaxation regime of (21) are plotted in Fig.2 (b) from a numerical integration of Eq.(16) for  $_{\rm p}=3.3$  fs,  $_{\rm F}=5$  meV and  $_{\rm R}$  ranging from 50 meV down to 1 meV.

To conclude, the kinetic equations describing the time evolution of the spin polarization have been formulated for arbitrary strength of the SO interaction. Explicit solutions for quantum wells with Rashba-like SO interactions predict the failure of the DP relaxation formula for su ciently strong SO couplings. In particular, the memory of the initial spin state can be strongly enhanced or reduced depending on  $_{\rm F}=_{\rm R}$ , suggesting an alternative route for spin manipulation in spintronic applications.

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E lectronic address: claudio grim aldill ep .ch

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